

A DETAILED PROCEDURE FOR PARAMETER EXTRACTION OF THE ONE-DIODE SOLAR CELL MODEL

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Many models for solar cells operation were developed on the basis of the Shockley theory of the illuminated p-n junction [1]. As a result, the equivalent circuit of the solar cell can be described at different levels of approximation. The one-diode model defines the most common approximation of the current-voltage (I-V) characteristics of a solar cell operating in standard test conditions (STC) (Fig. 1). STC specifies the global irradiance incident normal on the surface of a PV module at $G_{STC} = 1000 \text{ W/m}^2$ with a spectral distribution $AM1.5G$ and cell temperature $T_{STC} = 25^\circ\text{C}$. The equivalent circuit captures the physical process that governs the operation of a solar cell. The photocurrent (I_L) is modeled by a current source mainly depending on solar irradiance. The diode models the dark current losses (I_s). Current loss caused by increased junction conductivity at cell edges is modeled by the shunt resistance (R_P). The series resistance (R_S) captures the resistive losses in the cell such as the contact resistances and neutral regions resistances.

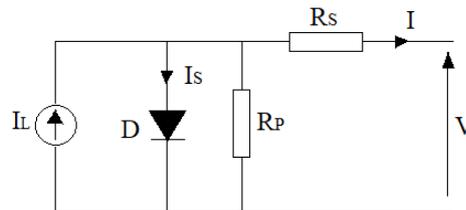


Fig. 1. One-diode model of a solar cell: the electrical circuit.

The most popular equation developed in the frame of one-diode model is the five-parameter equation:

$$I(V) = I_L - I_s \left[\exp\left(\frac{e(V + IR_S)}{mk_B T}\right) - 1 \right] - \frac{V + IR_S}{R_P} \quad (1)$$

where e is the elementary charge and k_B is the Boltzmann constant.

The I-V characteristics of a PV module consist of a superposition of the I-V characteristics of its constituent solar cells. A PV module is usually delivered by manufacturer with a datasheet which emphasizes three notable points on the I-V characteristic: the short-circuit current, the open-circuit voltage and the maximum power point (MPP). These points are measured at STC.

In this paper a detailed procedure [2] for parameters extraction is presented and assessed from the perspective of performance in modeling the I-V characteristics. The procedure uses only the information provided in datasheets, i.e the three notable points of the I-V characteristic. For this, the numerical results are compared with measured data. The samples were prepared at ISC Konstanz and characterized at the PV Laboratory of the West University of Timisoara.

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- [1] S. Lineykin, M. Averbukh, A. Kuperman, An improved approach to extract the single-diode equivalent circuit parameters of a photovoltaic cell/panel, *Renew Sustain Energy Rev* **30**, 282-289 (2014).
[2] A. Sabadus, V. Mihailetchi, M. Paulescu, Parameter extraction for the one-diode model of a solar cell, *American Institute of Physics Proceedings Series*, article number: 040005 (2017).